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(54) Title: SILICON OXYNITRIDE FILM

(57) Abstract

An oxynitride film on the surface of a silicon or silicon germanium substrate is described where film is substantially an oxide film at the film oxide interface, and the nitrogen content of the film increases with the distance away from the substrate. The film is made by a process of rapidly processing a clean silicon wafer in an atmosphere of a nitrogen containing a very small percentage of oxygen containing gas.